

Design Considerations and Noise Issues for Heterogeneous Contactless 3-D ICs

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Outline

- Contactless 3-D Integration
- Interference due to Inductive Links
- Crosstalk Noise in Contactless ICs
- Design of Heterogeneous Inductive Links
- Summary

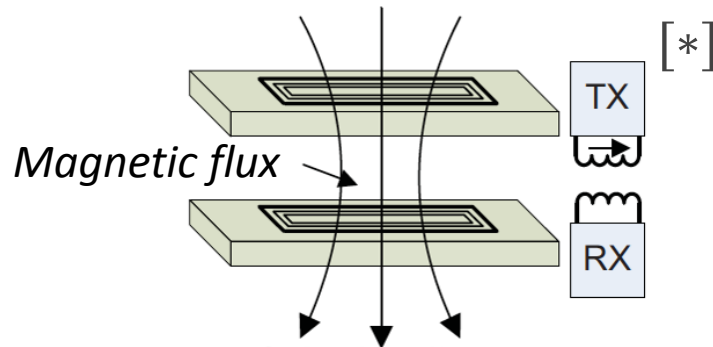
Contactless 3-D ICs

- Alternative to wired 3-D implementations
- Several advantages over TSV and microbumps
 - Compatible with standard CMOS lithography
 - No need for level shifters
 - Reduced ESD protection
- Stacking at affordable cost
- EM field coupled interfaces
 - Inductive links
 - Capacitive links

Contactless Inter-Tier Interfaces

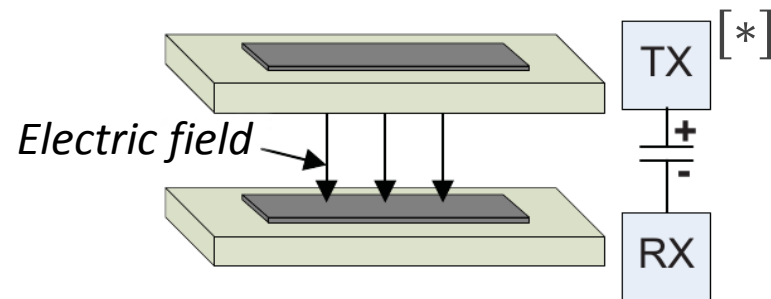
Inductive links

- Manipulates magnetic flux between on-chip inductors
- Current driven
- Long communication distances
- Support multiple integration styles



Capacitive links

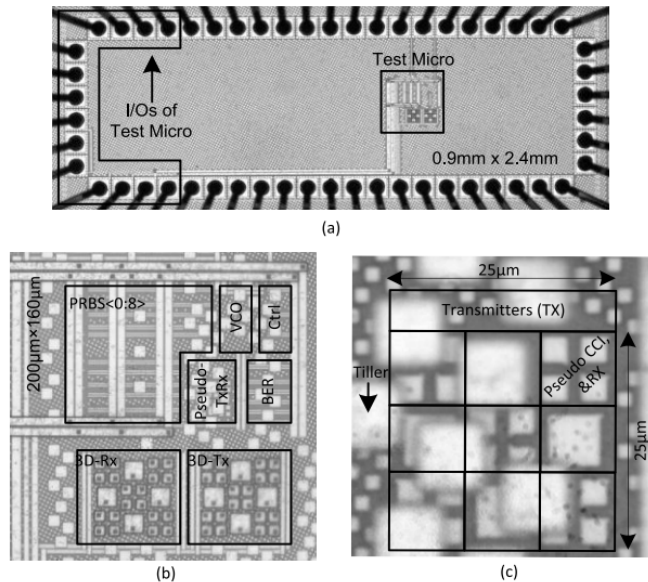
- Manipulates electric field between capacitor plates
- Voltage driven
- Short communication distances
- Limited to face-to-face integration



[*] J. Ouyang et al, "Evaluation of Using Inductive/Capacitive Coupling Vertical Interconnects in 3-D Network-on-Chip," *Proceedings of the International Conference on Computer-Aided Design*, pp. 477-482, November 2010.

State-of-the-Art Capacitive Links

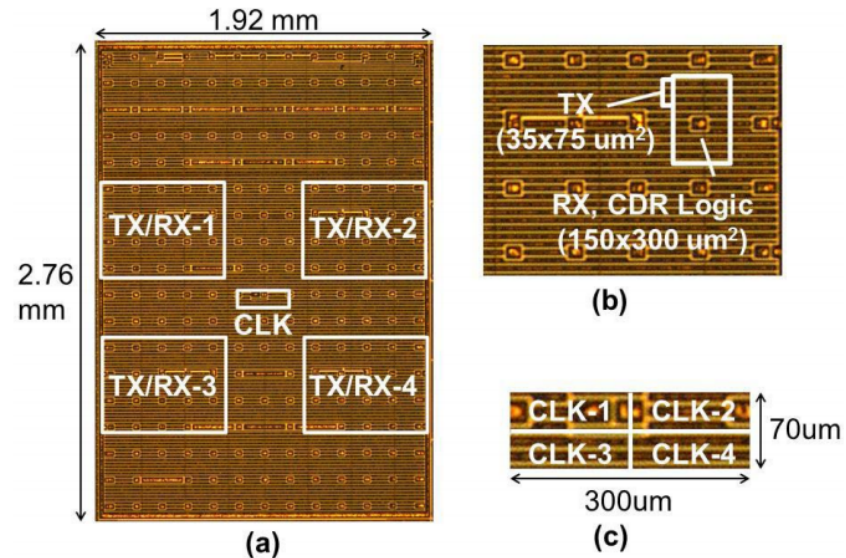
- Crosstalk cancelled capacitive coupling



- 65 nm process
- 2.31 Gb/s/ch
- 53 $\mu\text{W}/\text{Gb/s}$

Aung et al., "2.31-Gb/s/ch Area-Efficient Crosstalk Cancelled Hybrid Capacitive Coupling Interconnect for 3-D Integration," *IEEE Transactions of Very Large Scale Integration*, Vol. 24, No. 8, pp. 2703-2711, August 2016.

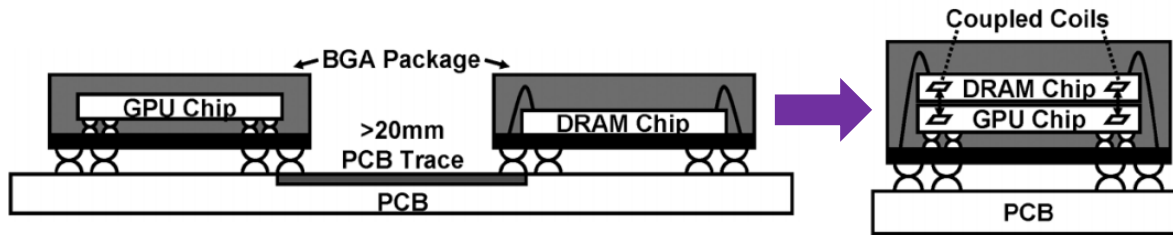
- Bi-directional 4 channel capacitive link



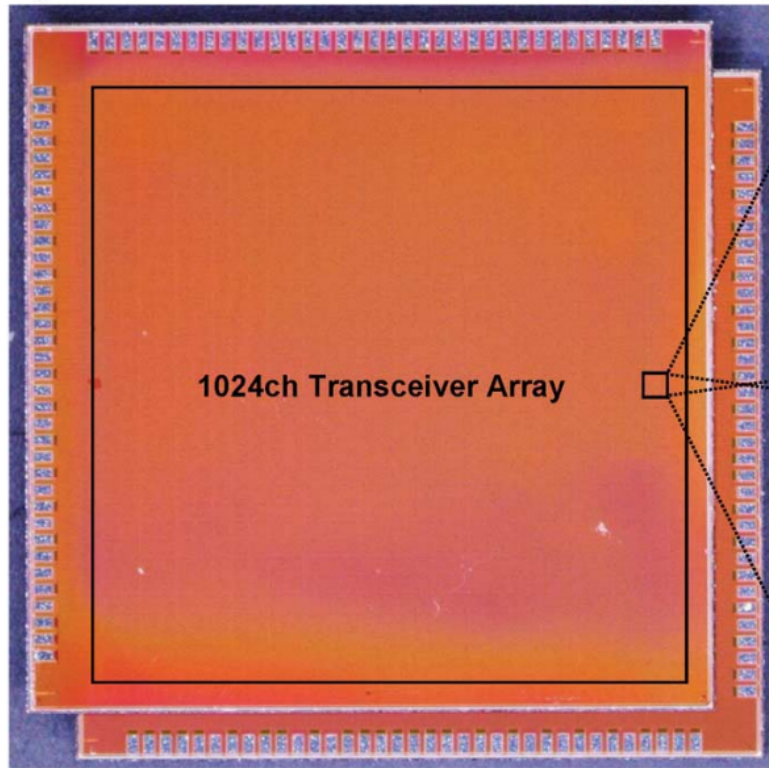
- 14 nm process
- 32 Gb/s
- 4 pJ/bit

Thakkar et al., "A 32 Gb/s Bidirectional 4-channel 4pJ/b Capacitively Coupled Link in 14 nm CMOS for proximity Communication," *IEEE Journal of Solid-State Circuits*, Vol. 51, No. 12, pp. 3231-3245, December 2016.

State-of-the-Art Inductive Links

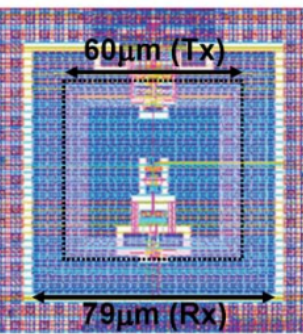
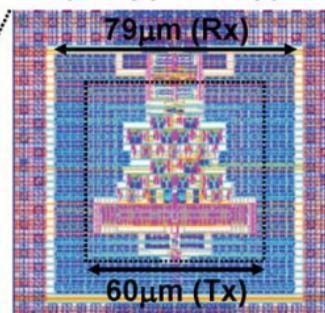


20 μ m-Thick Emulated-100nm DRAM Chip (Upper Chip)



65nm CMOS GPU Chip (Lower Chip)

DRAM Transceiver
(in Upper Chip)



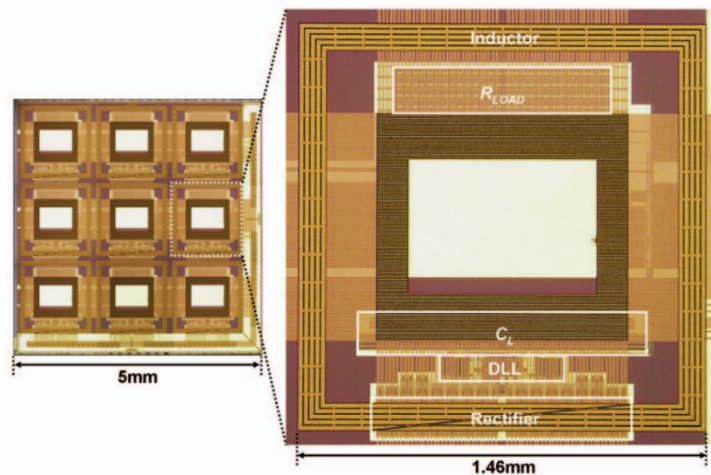
GPU Transceiver
(in Lower Chip)

- 1 TB/s from 1024 transceivers
- 1 pJ/bit
- 20 μ m separation distance
- BER < 10^{-16}
- 65 nm process

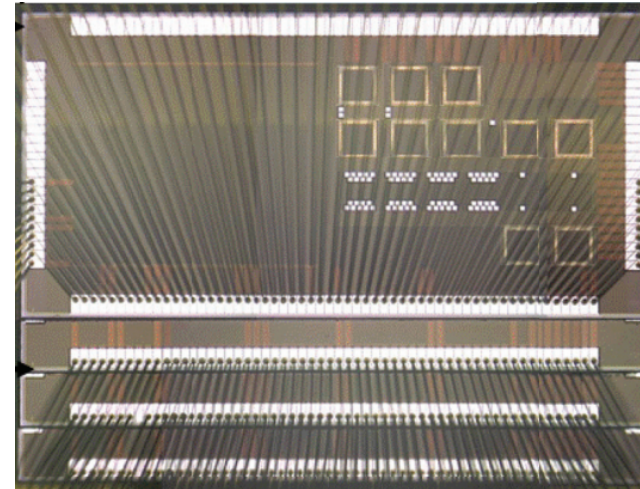
N. Miura et al., "A 1 TB/s 1 pJ/b 6.4 mm²/TB/s QDR Inductive Coupling Interface Between 65-nm CMOS Logic and Emulated 100-nm DRAM," *IEEE Journal on Emerging and Selected Topics in Circuits and Systems*, Vol. 2, No. 2, pp. 249-256, June 2012.

Applications of Inductive Links

- Non-contact wafer level testing



- 3-D multicore CPU

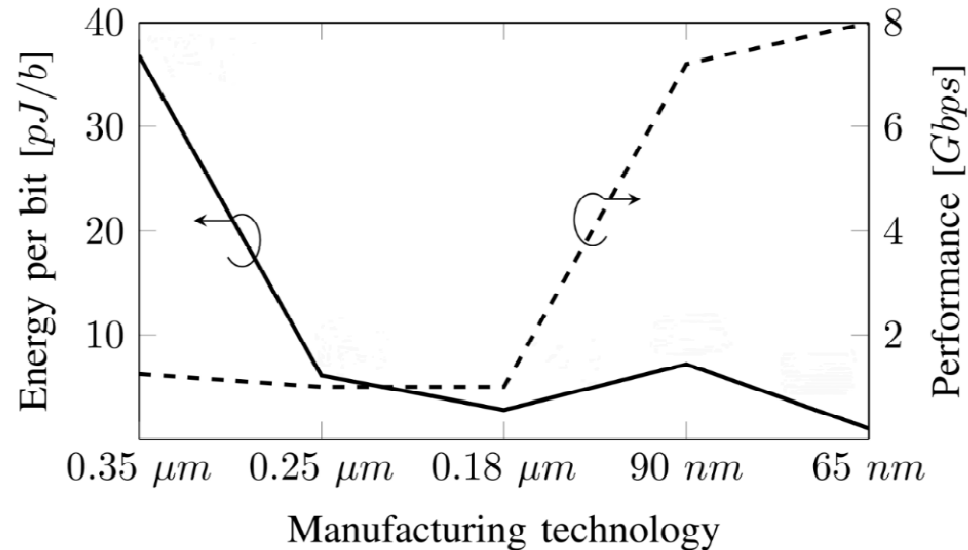


- Potential platforms for novel inductive links include
 - Internet of things edge devices
 - Biomedical circuits and micro-fluidic sensors

A. Radecki et al., "6W/25mm² Inductive Power Transfer for Non-Contact Wafer-Level Testing," *Proceedings of the International Solid-State Circuits Conference*, pp. 230-233, February 2011.

N. Miura et al., "A Scalable 3D Heterogeneous Multi-Core Processor with Inductive-Coupling ThruChip Interface," *Proceedings of IEEE Cool Chips XVI*, pp. 1-3, April 2013.

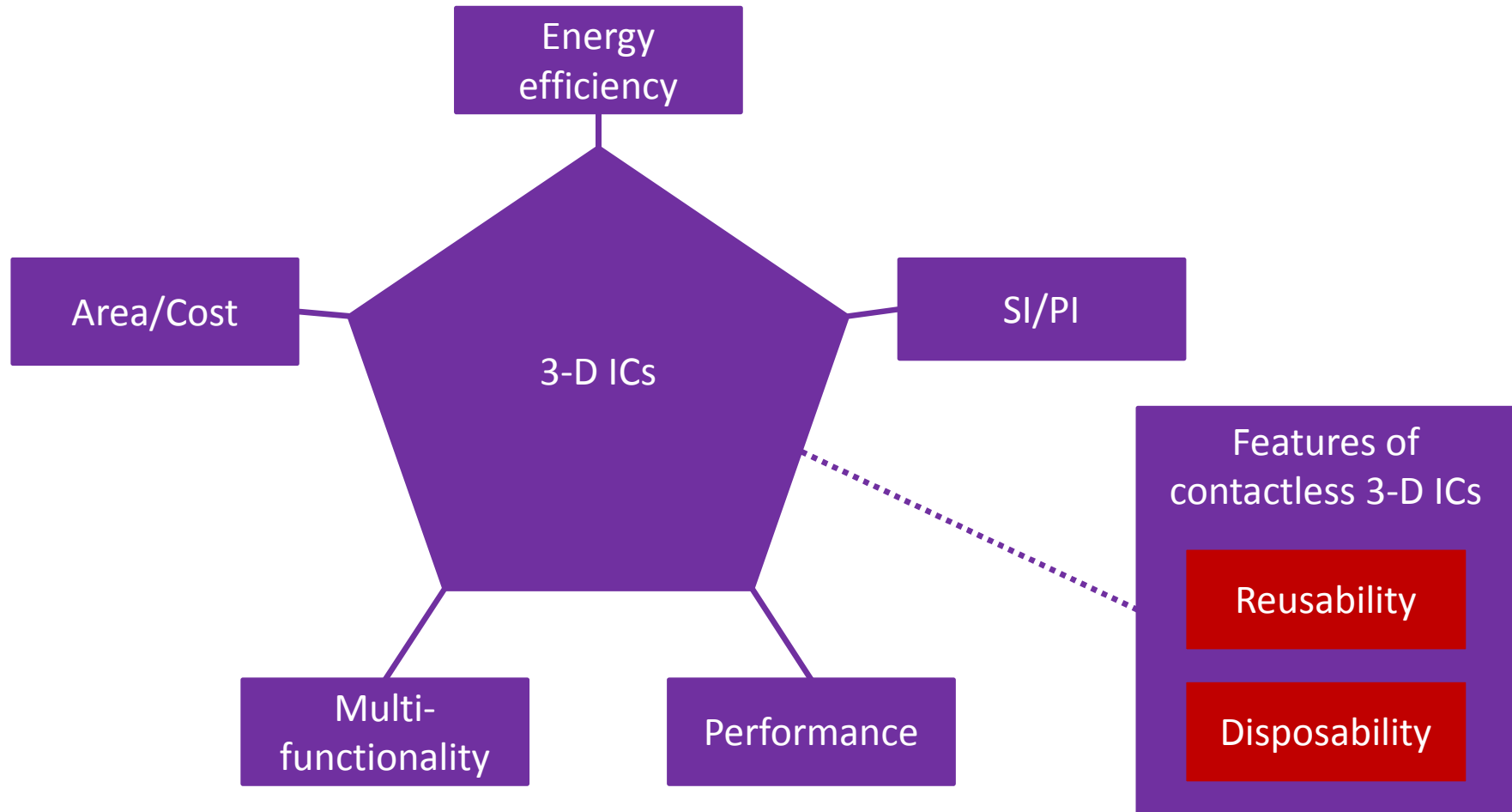
Evolution of Inductive Links



- Logic-memory applications
- Energy per bit
 - 1 pJ/bit
- Maximum performance
 - 8 Gbps

- Heterogeneous contactless systems have not been investigated
- Design considerations differ for heterogeneous systems

Design Space for (3-D) ICs



Challenges in Inductive Link Design

- Interference with noise sensitive components in the vicinity requires attention
- Crosstalk effects due to inductive links can affect inter-tier communication and power integrity
- Large currents flowing the inductor induce thermal effects and possible reliability issues
- Scaling in deep-submicrometer technologies is demanding
 - On-chip interconnects exhibit increasing resistance
 - Low voltage operation requires complex transceivers

Outline

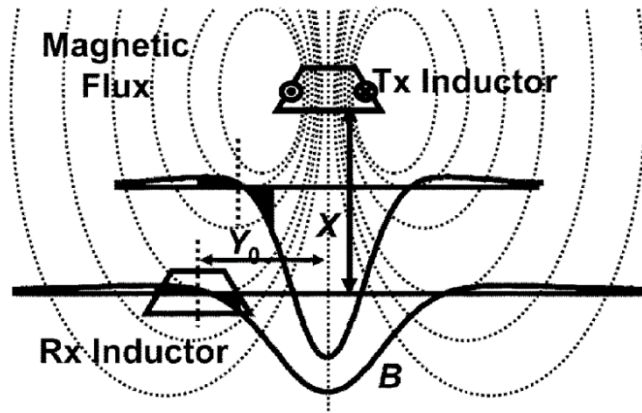
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Inductive Link Interference

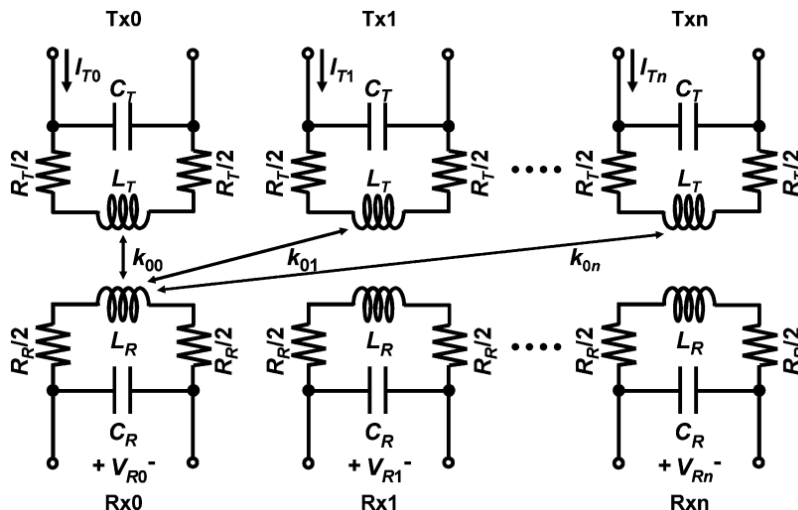
- Wireless signals couple with nearby circuits & interconnects
- Interference between inductive links is not negligible
- Effect varies depending upon the nature of “victim” circuit
- “Victim” circuits can be categorized as
 - Nearby inductive links
 - Digital circuits
 - Analog and sensing circuits
 - Signal and power on-chip interconnects

Interference on Neighboring Inductive Links

[*]



- Crosstalk to adjacent links similar to received signal (50 mV)
- Solutions to reduce crosstalk
 - Increase distance between links
 - Not suitable for high density applications
 - Time division interleaving technique
 - Maximum division depends upon performance constraints
 - 4-phase division sufficiently mitigates crosstalk



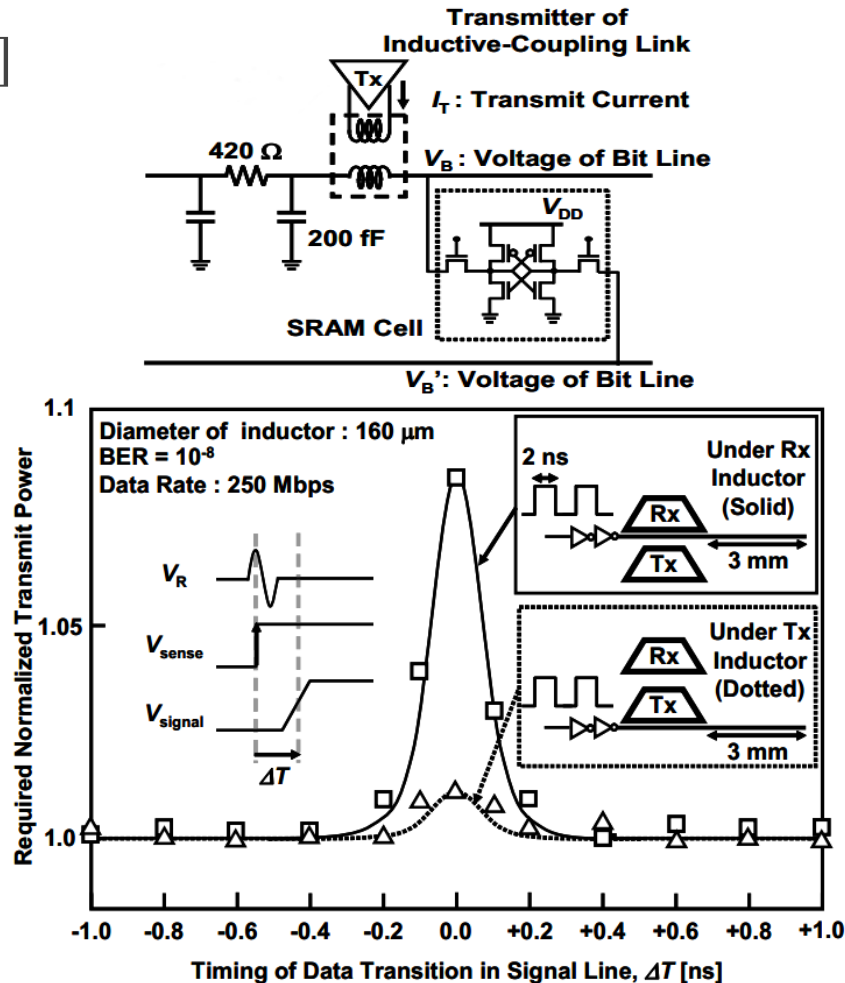
For 1 *Gbps* datarate time division

- 2-phase \Rightarrow crosstalk of 25 mV
- 4-phase \Rightarrow crosstalk of 10 mV

[*] – N. Miura et al., “Crosstalk Countermeasures for High-Density Inductive-Coupling Channel Array,” *IEEE Journal of Solid-State Circuits*, Vol. 42, No. 2, pp. 410-421, February 2007.

Interference on Circuit Components

[*]



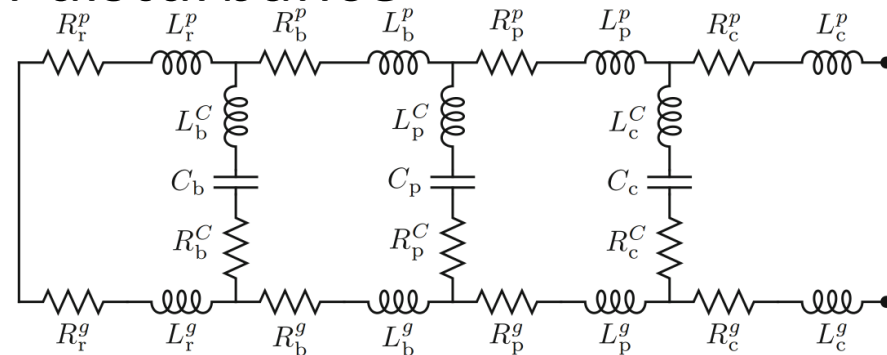
- Noise on digital circuits
 - Coupling through local interconnects
 - Crosstalk on local interconnects is negligible
 - $< 1 \text{ mV}$
- Noise on global interconnects is significant
- Power integrity may be compromised in high density interfaces

[*] – K. Niitsu et al., "Interference from Power/Signal Lines and to SRAM Circuits in 65nm CMOS Inductive-Coupling Link," IEEE Asian Solid-State Circuits Conference, pp.131-134, November 2007.

Power Integrity in Contactless 3-D Circuits

- On-chip power distribution networks (PDN)
 - Include regular topologies
 - Contain long wire segments
- Power integrity includes two types of noise
 - Resistive noise, IR drop
 - Device switching noise, $L \frac{di}{dt}$
- For contactless 3-D systems inductively induced noise can be another source of disturbance

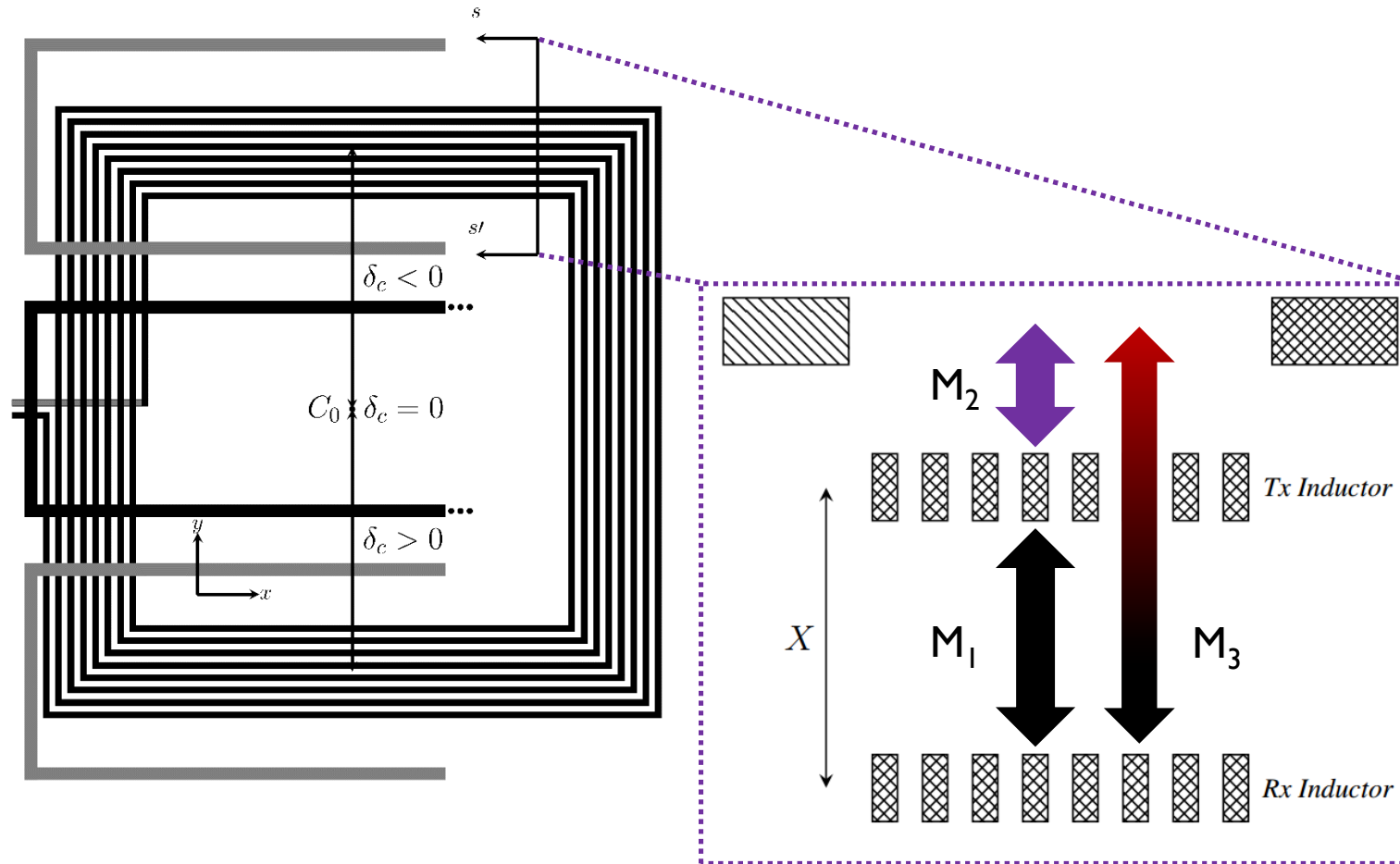
- Model the induced noise
- Efficiently analyse complex structures



Outline

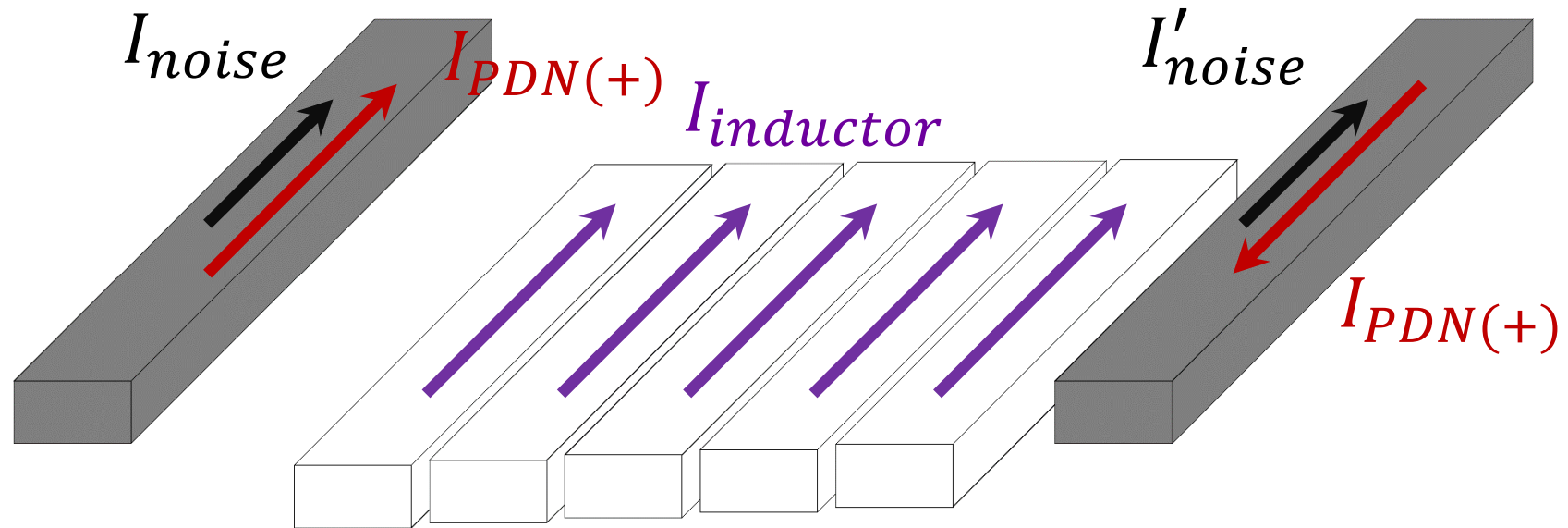
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Typical Inductor & PDN Structure



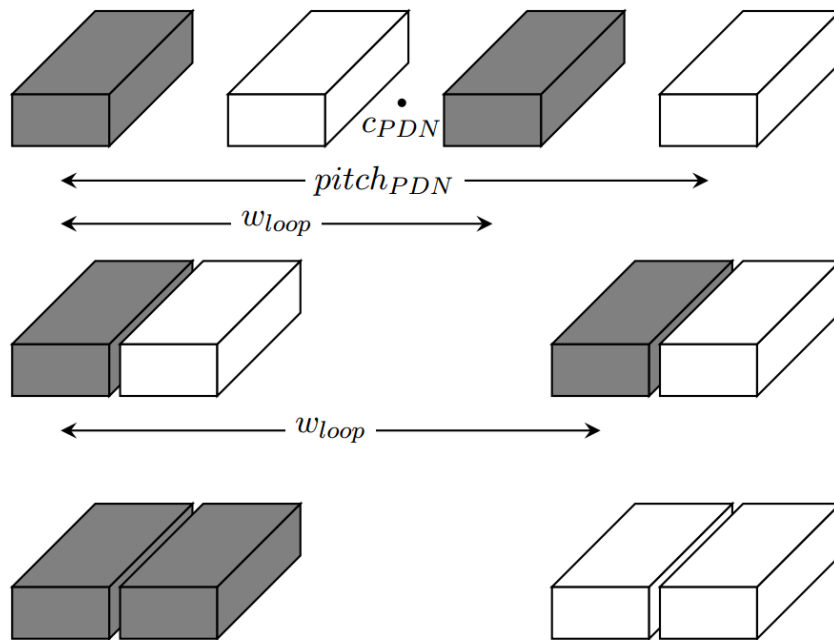
[*] – I. A. Papistas, V. F. Pavlidis “Crosstalk Noise effects of On-Chip Inductive Links on Power Delivery Networks, Proceedings of the IEEE International Symposium on Circuits and Systems, pp. 1937-1941, May 2016.

Induced Crosstalk Noise



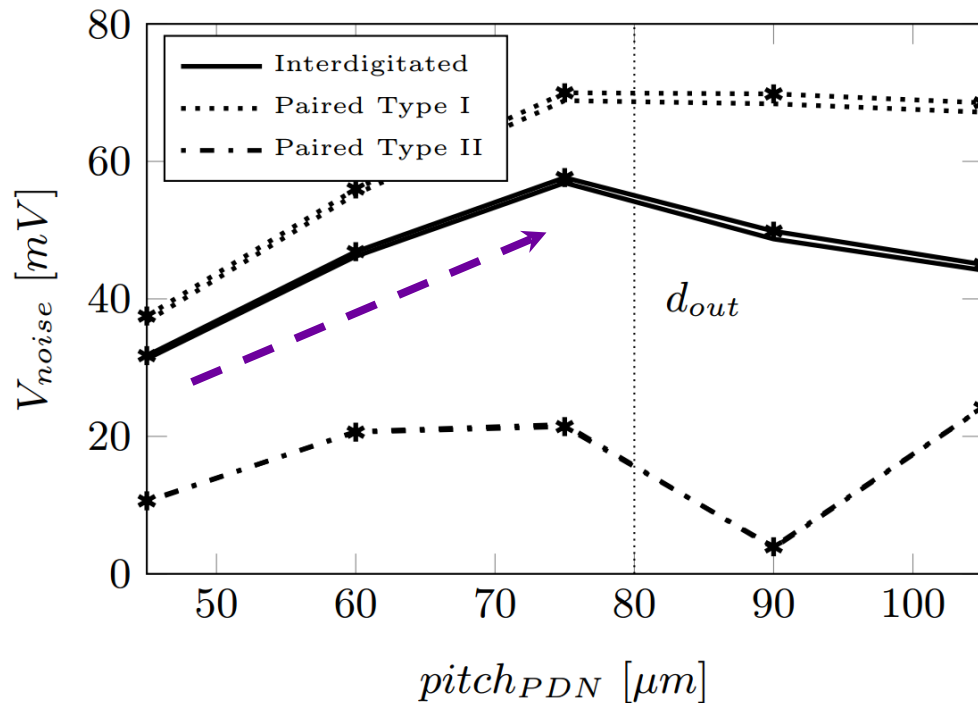
- $I_{PDN,acc} = I_{PDN} + (I_{noise} - I'_{noise})$
- Total induced current is minimised

PDN Topologies



- Different PDN topologies have been explored
 - Interdigitated
 - P-G/P-G, paired type I
 - P-P/G-G, paired type II
- Paired type II exhibits overall lowest susceptibility

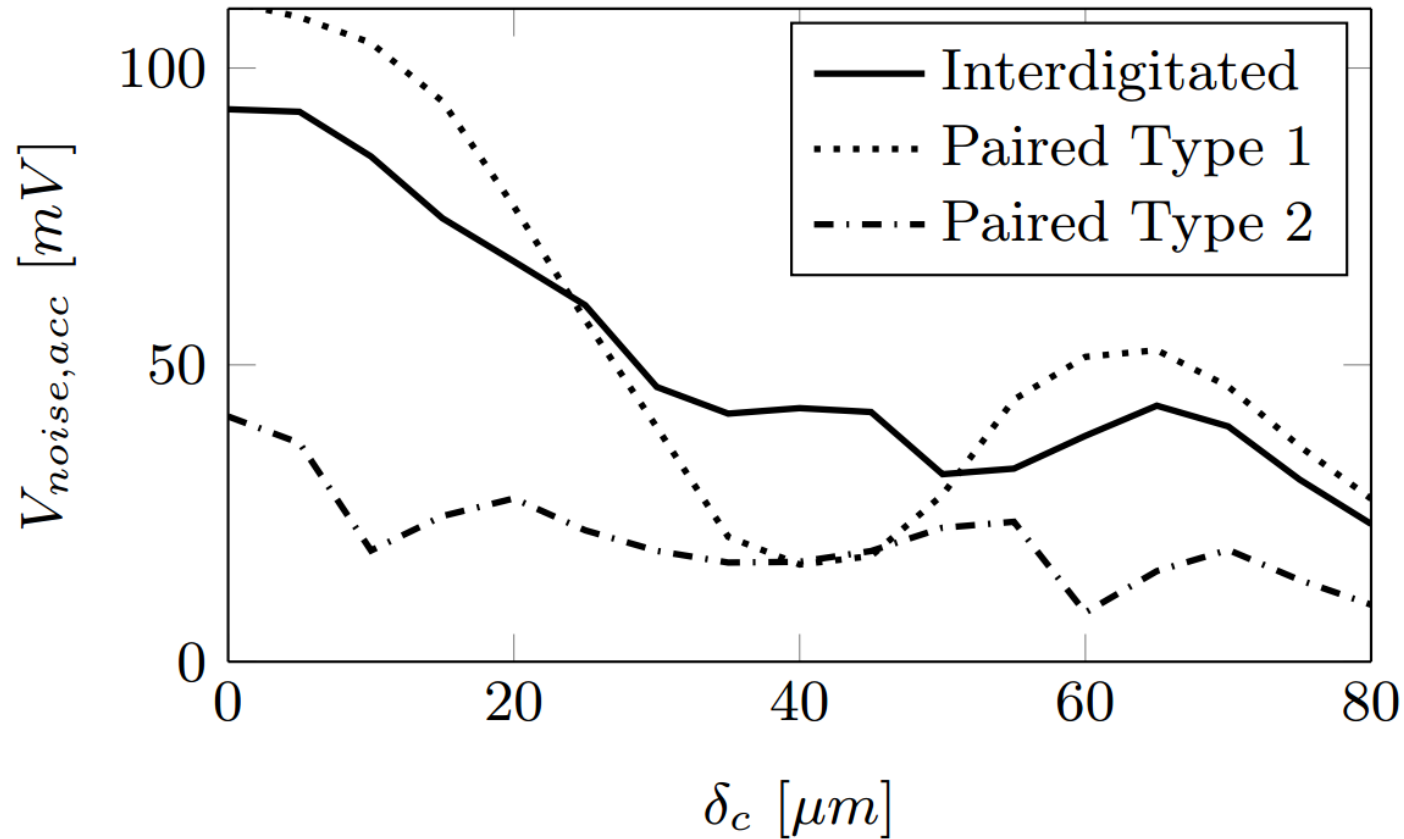
Crosstalk Noise – PDN Pitch



- For $pitch_{PDN} < d_{out}$
 - Noise increases with pitch
- As $pitch_{PDN} > d_{out}$
 - Noise is reduced
- Paired type I presents highest noise susceptibility
- Paired type II the lowest

[*] – I. A. Papistas, V. F. Pavlidis “Inter-Tier Crosstalk Noise On Power Delivery Networks for 3-D ICs with Inductively-Coupled Interconnects, Proceedings of the ACM Great Lakes Symposium, pp. 257-262, May 2016.

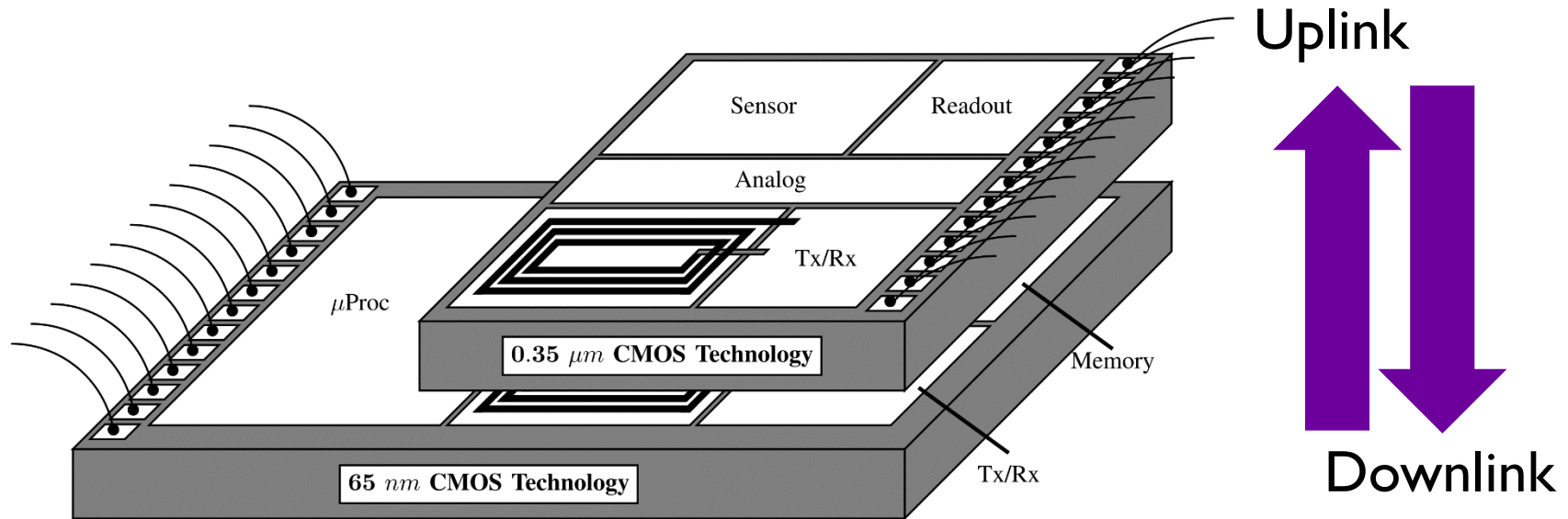
Crosstalk Noise for Varying δ_c



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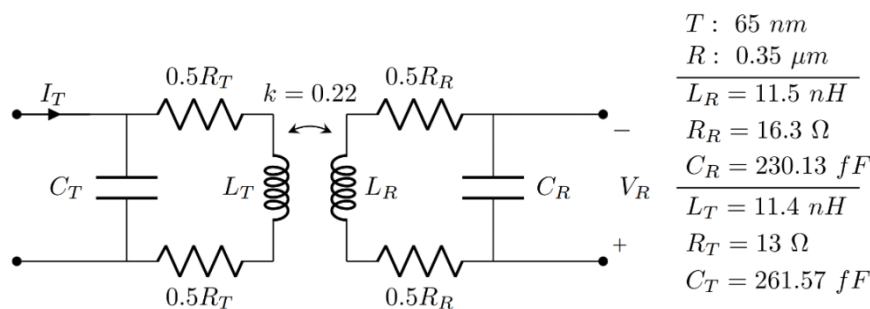
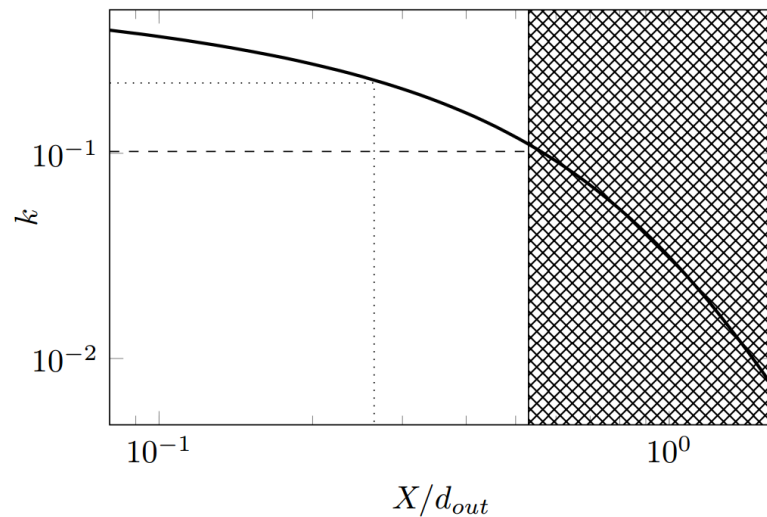
Heterogeneous Contactless Stacked Circuit



- Processing tier in 65 nm
- Sensing tier in 0.35 μ m
- Stacked face-up for fluidic sensing applications
- Half duplex communication supported
- Substrate thinned to 80 μ m

[*] – I. A. Papistas, V. F. Pavlidis “Contactless Inter-Tier Communication for Heterogeneous 3-D ICs, Proceedings of the IEEE International Symposium on Circuits and Systems, pp. 2585-2588, May 2017.

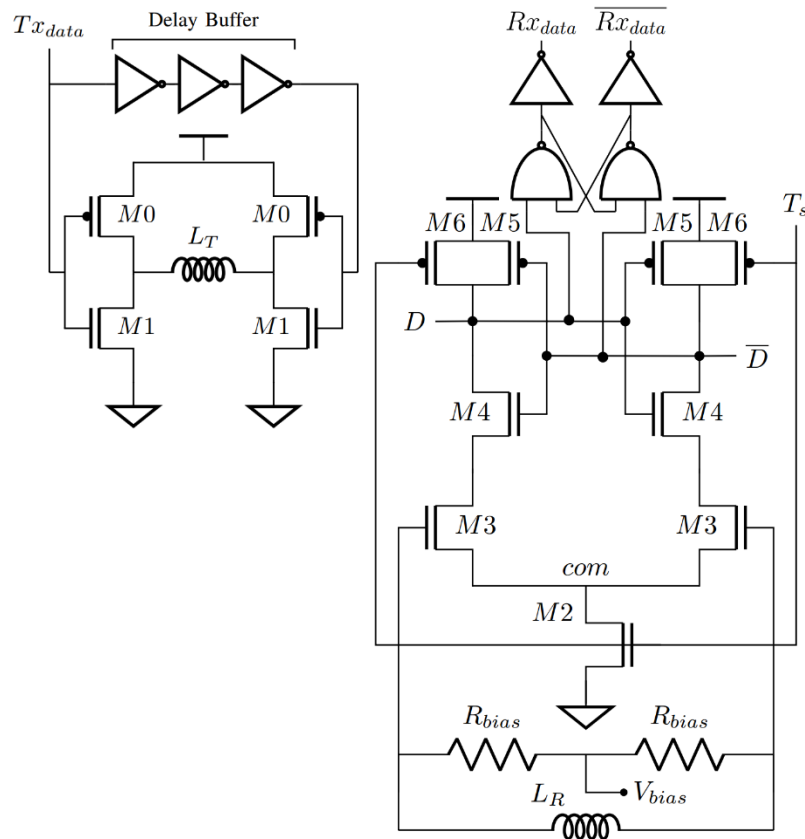
Area Considerations



- Coupling depends upon outer diameter and communication distance
- Minimum coupling $k = 0.1$
- This example
 - $k = 0.22$
 - $d_{out} = 300 \text{ } \mu\text{m}$
- DRC/DFM free inductor layout using VeloceRF*
- Both inductors used for data transmission and reception

*VeloceRF User Manual, v2, Helic, Inc., November 2013.

Transceiver Circuit

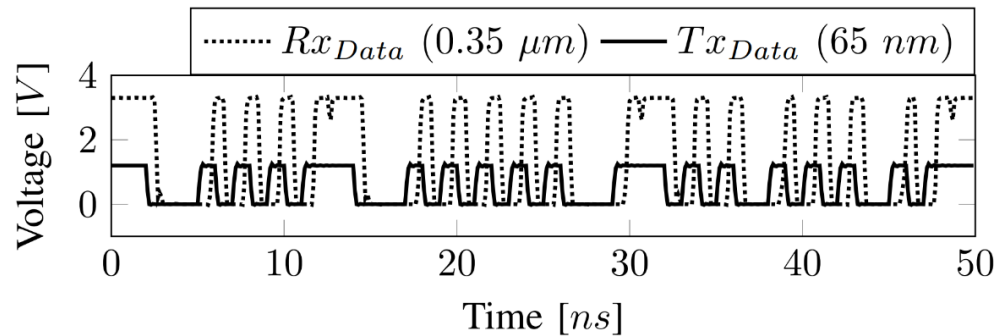


- Transceiver circuit
 - H-Bridge transmitter
 - Sense amplifier receiver
- Received pulse is sampled within a specified time interval
 - Crosstalk noise and accidental switches are reduced
- Biasing of differential pair important for circuit operation

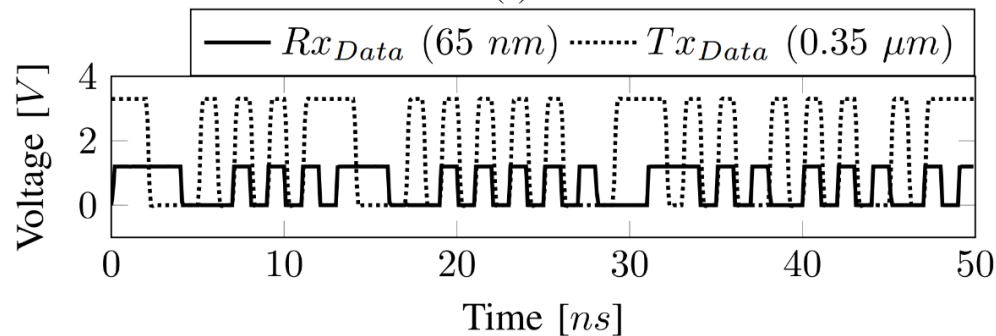
Methodology for Power Efficiency

- Power efficiency is the primary objective
 - $P_{tot} = P_{Tx65} + P_{Tx350} + P_{Rx65} + P_{Rx350}$
- Two design approaches can be followed
 - Minimization of each power component individually
 - Consideration of core voltage in each process node
- Tradeoff between power and sensitivity exists
 - 0.35 μm tier sized for minimum power
 - Sensitivity of 300 mV
 - 65 nm tier sized for highest sensitivity
 - Sensitivity of 75 mV
- 70% decrease in 0.35 μm device width is achieved

Simulation Results



(a)



- Full swing signal at nominal voltage
- No level shifters required

- $P_{\text{uplink}} = 5.28 \text{ mW}$
 - $P_{\text{uplink, avg}} = 2.5 \text{ mW}$

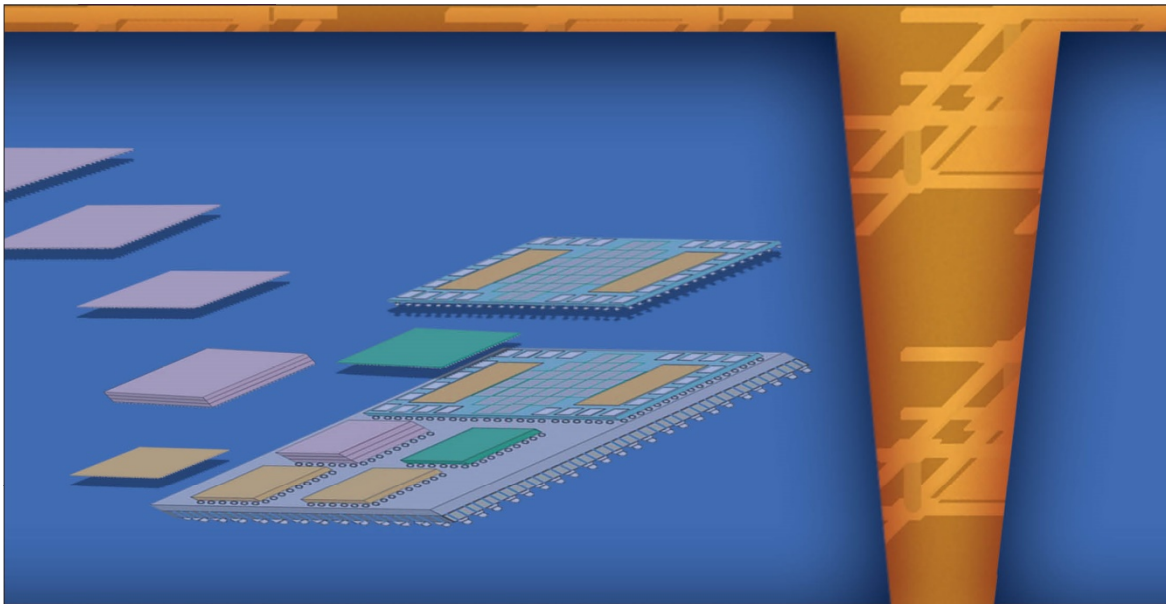
- $P_{\text{downlink}} = 8.67 \text{ mW}$
 - $P_{\text{downlink, avg}} = 2.38 \text{ mW}$

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Summary

- Inductive links crosstalk noise on PDNs is not negligible
- PDN topologies exhibit different sensitivity to noise
- Noise-aware PDN placement can suppress this type of induced noise up to 70%
- The design space changes for heterogeneous 3-D ICs
- Exploiting the sensitivity versus power tradeoff
 - Significant decrease in device sizes and therefore in power is achieved



THREE-DIMENSIONAL INTEGRATED CIRCUIT DESIGN

2ND EDITION

Available: mid-July 2017
Morgan Kaufmann Publishers

Thank you!

MK
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